



## SOT-23 Plastic-Encapsulate Transistors

**S8550LT1** TRANSISTOR ( PNP )

### FEATURES

Power dissipation

$P_{CM} : 0.3 \text{ W (Tamb=25}^{\circ}\text{C)}$

Collector current

$I_{CM} : -0.5 \text{ A}$

Collector-base voltage

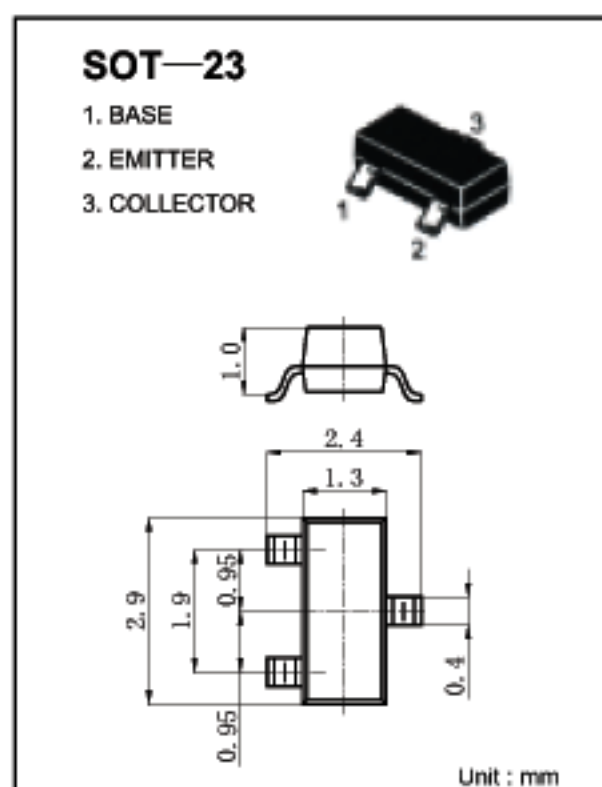
$V_{(BR)CBO} : -40 \text{ V}$

Operating and storage junction temperature range

$T_J, T_{stg} : -55^{\circ}\text{C to } +150^{\circ}\text{C}$

### ELECTRICAL CHARACTERISTICS ( Tamb=25 °C

unless otherwise specified)



Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CB}$ O	$I_C = -100 \mu\text{A}, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CE}$ O	$I_C = -0.1\text{mA}, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu\text{A}, I_C = 0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -40 \text{ V}, I_E = 0$		-0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -20 \text{ V}, I_B = 0$		-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -3 \text{ V}, I_C = 0$		-0.1	$\mu\text{A}$
DC current gain	$H_{FE(1)}$	$V_{CE} = -1 \text{ V}, I_C = -50 \text{ mA}$	120	350	
	$H_{FE(2)}$	$V_{CE} = -1 \text{ V}, I_C = -500 \text{ mA}$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$ )	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$ )	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		-1.2	V
Base-emitter voltage	$V_{BEF}$	$I_E = -100 \text{ mA}$		-1.4	V
Transition frequency	$f_T$	$V_{CE} = -6 \text{ V}, I_C = -20 \text{ mA}$  $f = 30 \text{ MHz}$	150		MHz

### CLASSIFICATION OF $H_{FE(1)}$

Rank	L	H
Range	120-200	200-350

**DEVICE MARKING : S8550LT1=2TY**